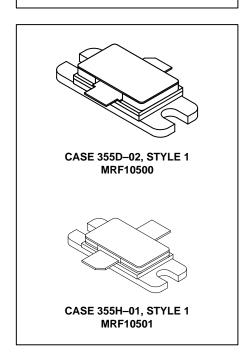
The RF Line Microwave Pulse Power Transistors

... designed for 1025-1150 MHz pulse common base amplifier applications such as TCAS, TACAN and Mode-S transmitters.

- Guaranteed Performance @ 1090 MHz
 Output Power = 500 Watts Peak
 Gain = 8.5 dB Min, 9.0 dB (Typ)
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Hermetically Sealed Industry Package
- · Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- · Internal Input and Output Matching
- Characterized with 10 μs, 1% Duty Cycle Pulses

MRF10500 MRF10501

500 W (PEAK) 1025-1150 MHz MICROWAVE POWER TRANSISTORS NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCES	65	Vdc
Collector-Base Voltage	VCBO	65	Vdc
Emitter–Base Voltage	VEBO	3.5	Vdc
Collector Current — Peak (1)	lc	29	Adc
Total Device Dissipation @ T _C = 25°C (1), (2) Derate above 25°C	PD	1460 8.3	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +200	°C
Junction Temperature	TJ	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	$R_{\theta JC}$	0.12	°C/W

NOTES:

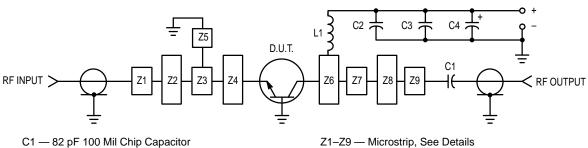
- 1. Under pulse RF operating conditions.
- 2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.
- 3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ_{JC} value measured @ 32 μs, 2%.)

REV 6



ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (I _C = 60 mAdc, V _{BE} = 0)	V(BR)CES	65	-	_	Vdc	
Collector-Base Breakdown Voltage (I _C = 60 mAdc, I _E = 0)	V(BR)CBO	65	-	_	Vdc	
Emitter–Base Breakdown Voltage (I _E = 10 mAdc, I _C = 0)	V(BR)EBO	3.5	_	_	Vdc	
Collector Cutoff Current (V _{CB} = 36 Vdc, I _E = 0)	ICBO	_	_	25	mAdc	
ON CHARACTERISTICS	ON CHARACTERISTICS					
DC Current Gain (I _C = 5.0 Adc, V _{CE} = 5.0 Vdc)	hFE	20	-	_	_	
FUNCTIONAL TESTS						
Common–Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{Out} = 500 W Peak, f = 1090 MHz)	G _{PB}	8.5	9.0		dB	
Collector Efficiency (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz)	η	40	45	_	%	
Load Mismatch (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Output Power				



C2 — 39 pF 100 Mil Chip Capacitor

C3 — 0.1 μF C4 — 100 μF , 100 Vdc, Electrolytic

L1 — 3 Turns #18 AWG, 1/8" ID, 0.18 Long

Z1-Z9 — Microstrip, See Details

Board Material — Teflon, Glass Laminate

Dielectric Thickness = 0.030"

 ϵ_{Γ} = 2.55, 2 Oz. Copper

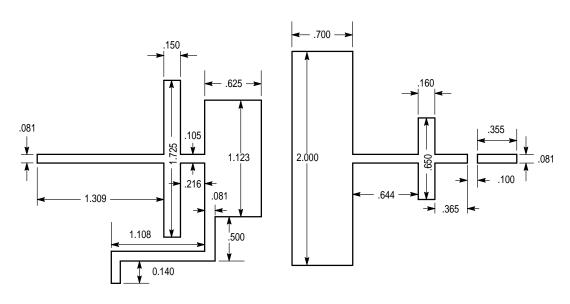


Figure 1. Test Circuit

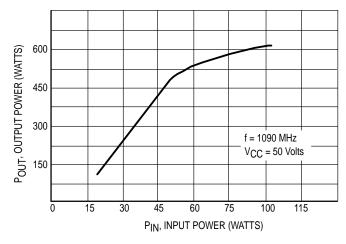
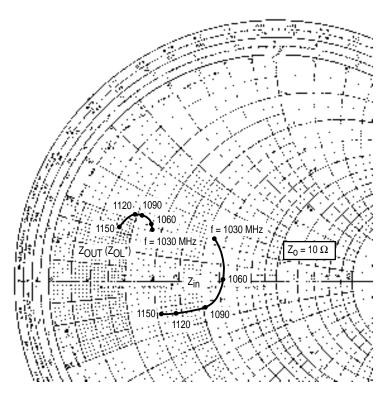


Figure 2. Output Power versus Input Power



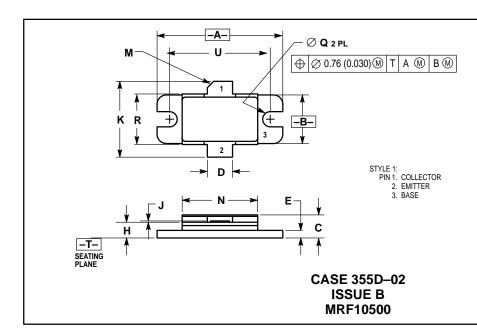
 $P_{OUT} = 500 \text{ W Pk} \quad V_{CC} = 50 \text{ V}$

	f MHz	Z _{in} OHMS	Z _{OL} * (Z _{OUT}) OHMS
I	1030	5.3 + j2.25	2.6 + j1.89
	1060	6.2 + j0.2	2.56 + j2.0
	1090	5.2 – j1.4	2.12 + j2.2
	1120	3.7 – j1.35	1.9 + j2.15
	1150	3.15 – j1.3	1.6 + j1.62

 $\mathbf{Z}_{OL}{}^{\star}$ is the conjugate of the optimum load impedance into which the device operates at a given output power voltage and frequency.

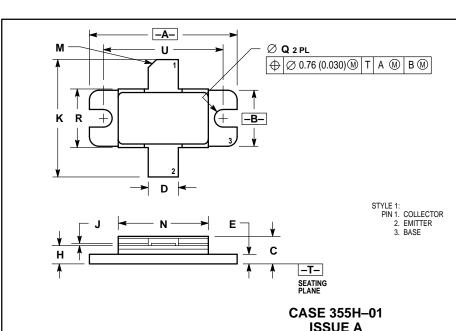
Figure 3. Series Equivalent Input/Output Impedances

PACKAGE DIMENSIONS



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.990	1.010	25.15	25.65	
В	0.375	0.395	9.53	10.03	
С	0.150	0.165	3.81	4.19	
D	0.195	0.205	4.95	5.21	
E	0.055	0.065	1.40	1.65	
H	0.120	0.130	3.05	3.30	
J	0.003	0.006	0.08	0.15	
K	0.570	0.630	14.48	16.00	
M	45 °REF		45°	45 °REF	
N	0.590	0.610	14.99	15.49	
Q	0.115	0.125	2.92	3.18	
R	0.395	0.405	10.03	10.29	
U	0.800 BSC		20.32	BSC	



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.990	1.010	25.15	25.65
В	0.375	0.395	9.53	10.03
C	0.150	0.165	3.81	4.19
ם	0.195	0.205	4.95	5.21
Е	0.055	0.065	1.40	1.65
Η	0.120	0.130	3.05	3.30
7	0.003	0.006	0.08	0.15
K	0.780	0.820	19.81	20.83
М	45° REF		45°	REF
N	0.590	0.610	14.99	15.49
ø	0.115	0.125	2.92	3.18
R	0.395	0.405	10.03	10.29
U	0.800 BSC		20.32	BSC

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